

This 5-line voltage transient suppressor array is designed for application requiring transient voltage protection capability. It is intended for use in over-transient voltage and ESD sensitive equipment such as computers, printers, automotive electronics, networking communication and other applications. This device features a monolithic common anode design which protects five independent lines in a single SOT-363 package.

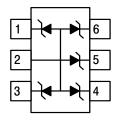
Features

- Protects up to 5-Line in a Single SOT-363 Package
- Peak Power Dissipation 100 W (8 x 20 µs Waveform)
- ESD Rating of Class 3B (Exceeding 8 kV) per Human Body Model and Class C (Exceeding 400 V) per Machine Model.
- Compliance with IEC 61000-4-2 (ESD) 15 kV (Air), 8 kV (Contact)
- Flammability Rating of UL 94 V-0
- Pb-Free Packages are Available*

Applications

- Hand-Held Portable Applications
- Networking and Telecom
- Automotive Electronics
- · Serial and Parallel Ports
- Notebooks, Desktops, Servers

PIN ASSIGNMENT



PIN1. CATHODE
2. ANODE
3. CATHODE4
. CATHODE5.
CATHODE6.
CATHODE

MAXIMUM RATINGS (T_J = 25°C unless otherwise specified)

Symbol	Rating	Value	Unit
P _{PK} 1	Peak Power Dissipation 8 x 20 μs Double Exponential Waveform (Note 1)	100	W
TJ	Operating Junction Temperature Range	-40 to 125	°C
T _{STG}	Storage Temperature Range	–55 to 150	°C
T_L	Lead Solder Temperature (10 s)	260	°C
ESD	Human Body Model (HBM) Machine Model (MM) IEC 61000-4-2 Air (ESD) IEC 61000-4-2 Contact (ESD)	16000 400 15000 15000	٧

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Nonrepetitive current pulse per Figure 3.



$\textbf{SMF05CT1G ELECTRICAL CHARACTERISTICS} \ (\textbf{T}_{J} = 25^{\circ} \text{C unless otherwise specified})$

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Reverse Working Voltage V _{RWM} (I		(Note 2)			5.0	V
Breakdown Voltage	V _{BR}	I _T = 1 mA, (Note 3)	6.2		7.2	V
Reverse Leakage Current	I _R	V _{RWM} = 5 V		0.07	5.0	μΑ
Clamping Voltage	V _C	I _{PP} = 5 A (8 x 20 μs Waveform)			9.8	V
Clamping Voltage	V _C	I _{PP} = 8 A (8 x 20 μs Waveform)			12.5	V
Maximum Peak Pulse Current	I _{PP}	8 x 20 μs Waveform			8.0	Α
Capacitance		V _R = 0 V, f = 1 MHz (Line to GND)		80	130	pF

$\textbf{SMF12CT1G ELECTRICAL CHARACTERISTICS} \ (T_J = 25^{\circ}\text{C unless otherwise specified})$

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Reverse Working Voltage	V_{RWM}	(Note 2)			12	V
Breakdown Voltage	V_{BR}	I _T = 1 mA, (Note 3)	13.3		15	V
Reverse Leakage Current	I _R	V _{RWM} = 12 V		0.01	0.1	μΑ
Clamping Voltage	V _C	I _{PP} = 3 A (8 x 20 μs Waveform)			21	V
Clamping Voltage	V _C	I _{PP} = 6 A (8 x 20 μs Waveform)			23	V
Maximum Peak Pulse Current	I _{PP}	8 x 20 μs Waveform			6.0	Α
Capacitance	CJ	V _R = 0 V, f = 1 MHz (Line to GND)		40	60	pF

$\textbf{SMF15CT1G ELECTRICAL CHARACTERISTICS} \ (T_J = 25^{\circ}\text{C}, \text{ unless otherwise specified})$

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Reverse Working Voltage	king Voltage V _{RWM} (Note 2)				15	V
Breakdown Voltage	V _{BR}	I _T = 1 mA, (Note 3)	17		19	V
Reverse Leakage Current	I _R	V _{RWM} = 15 V		0.01	1.0	μΑ
Clamping Voltage	V _C	I _{PP} = 1 A (8 x 20 μs Waveform)			23	V
Clamping Voltage	V _C	I _{PP} = 5 A (8 x 20 μs Waveform)			29	V
Maximum Peak Pulse Current	I _{PP}	8 x 20 μs Waveform			5.0	Α
Capacitance	CJ	V _R = 0 V, f = 1 MHz (Line to GND)		33	45	pF

$\textbf{SMF24CT1G ELECTRICAL CHARACTERISTICS} \ (T_J = 25^{\circ}\text{C}, \text{ unless otherwise specified})$

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Reverse Working Voltage	everse Working Voltage V _{RWM} (Not				24	V
Breakdown Voltage	V_{BR}	I _T = 1 mA, (Note 3)	26.7		32	V
Reverse Leakage Current	I _R	V _{RWM} = 24 V		0.01	1.0	μΑ
Clamping Voltage	V _C	I _{PP} = 1 A (8 x 20 μs Waveform)			40	V
Clamping Voltage	V _C	I _{PP} = 2.5 A (8 x 20 μs Waveform)			44	V
Maximum Peak Pulse Current	I _{PP}	8 x 20 μs Waveform			2.5	Α
Capacitance		V _R = 0 V, f = 1 MHz (Line to GND)		21	25	pF

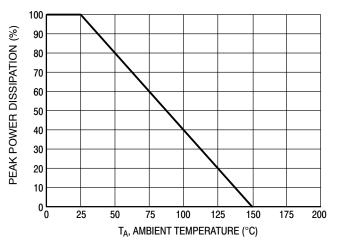
^{2.} TVS devices are normally selected according to the working peak reverse voltage (V_{RWM}), which should be equal or greater than the DC or continuous peak operating voltage level.

3. V_{BR} is measured at pulse test current I_T.



TYPICAL PERFORMANCE CURVES

(T_J = 25°C unless otherwise specified)





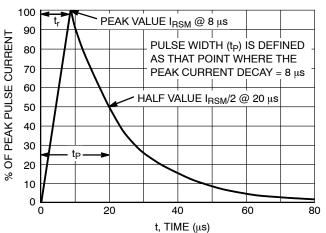


Figure 2. $8 \times 20 \mu s$ Pulse Waveform

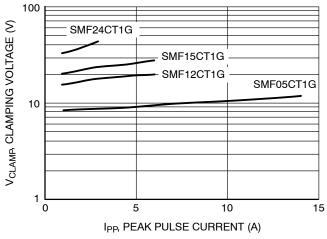


Figure 3. Clamping Voltage vs Peak Pulse Current

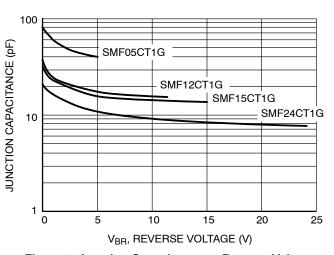
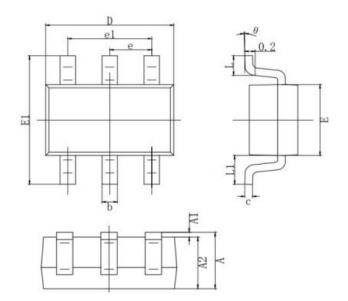


Figure 4. Junction Capacitance vs Reverse Voltage



SOT-363 PACKAGE OUTLINE DIMENSIONS



	MILLIMETER		
SYMBOL	MIN	MAX	
A	0.900	1. 100	
A1	0.000	0. 100	
A2	0.900	1.000	
b	0, 150	0.350	
c	0.080	0. 150	
D	2.000	2. 200	
Е	1.150	1. 350	
E1	2. 150 2. 45		
e	0.65	0 TYP.	
e1	1. 200	00 1.400	
L	0.52	5 REF.	
LI	0.260	0.460	
θ	0*	8*	

Ordering information

Order code	Package	Baseqty	Deliverymode
UMW SMF05CT1G	SOT-363	3000	Tape and reel
UMW SMF12CT1G	SOT-363	3000	Tape and reel
UMW SMF15CT1G	SOT-363	3000	Tape and reel
UMW SMF24CT1G	SOT-363	3000	Tape and reel

单击下面可查看定价,库存,交付和生命周期等信息

>>UMW(友台半导体)